

# NPN SILICON RF TRANSISTOR

**DESCRIPTION:**

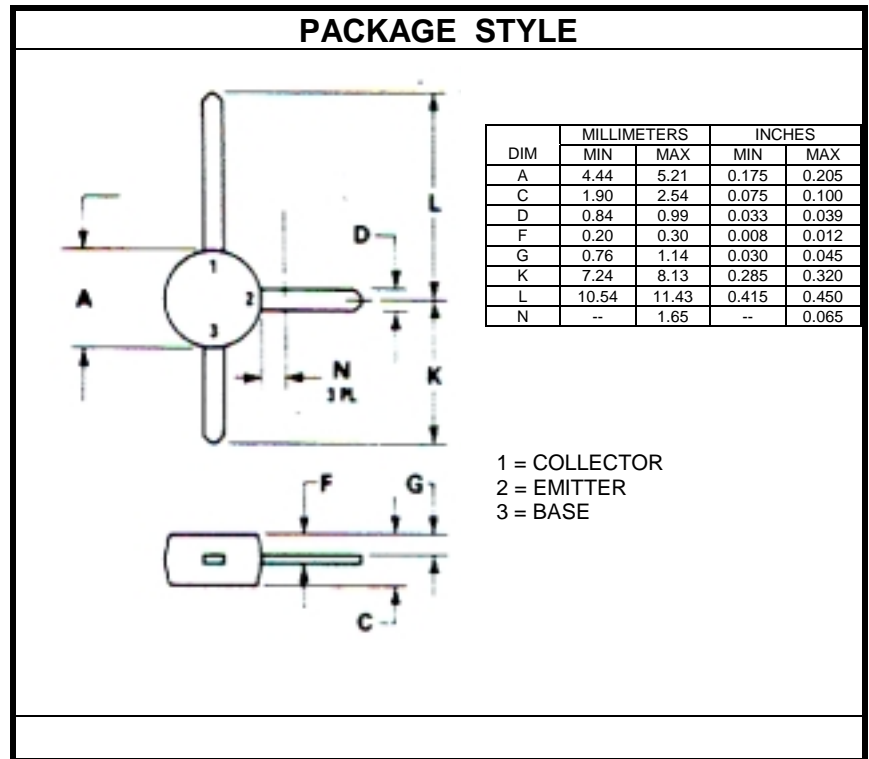
The **ASI MRF962** is designed for Low-to-medium power amplifier applications, requiring high gain, low noise figure, and low intermodulation distortion.

**FEATURES:**

- **NF** = 2.0 dB
- **Omnigold™** Metalization System
- Hermetic stripline, ceramic package

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	100 mA
<b>V<sub>CB</sub></b>	20 V
<b>P<sub>DISS</sub></b>	.75 W @ T <sub>C</sub> = 100 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	133 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA			15			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA			20			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 100 μA			3.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 10 V					100	<b>nA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 50 mA		30		200	<b>---</b>
<b>C<sub>CB</sub></b>	V <sub>CB</sub> = 10 V	f = 1.0 MHz			1.2	1.5	<b>pF</b>
<b>f<sub>t</sub></b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 50 mA	f = 0.5 GHz		4.5		<b>GHz</b>
<b>NF</b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 10 mA	f = 0.5 GHz		2.0		<b>dB</b>